

• This device is available in Pb-free package(s). Specifications herein apply to both standard and Pb-free devices. Please see our website at www.onsemi.com for specific Pb-free orderable part numbers, or contact your local ON Semiconductor sales office or representative.

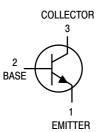
#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	15	Vdc
Collector – Emitter Voltage	V <sub>CES</sub>	40	Vdc
Collector – Base Voltage	V <sub>CBO</sub>	40	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current — Continuous — 10 µs Pulse	Ι <sub>C</sub>	300 500	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C



**ON Semiconductor Preferred Device** 





#### **THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage	$(I_{C} = 100 \ \mu Adc, \ V_{BE} = 0)$	V <sub>(BR)CES</sub>	40	—	Vdc
Collector – Emitter Sustaining Voltage <sup>(1)</sup>	(I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	15	—	Vdc
Collector – Base Breakdown Voltage	$(I_{C} = 100 \ \mu Adc, I_{E} = 0)$	V <sub>(BR)CBO</sub>	40	—	Vdc
Emitter – Base Breakdown Voltage	$(I_E = 100 \ \mu Adc, \ I_C = 0)$	V <sub>(BR)EBO</sub>	5.0	—	Vdc
Collector Cutoff Current ( $V_{CE} = 20 \text{ Vdc}, V_{BE} = 0$ ) ( $V_{CE} = 20 \text{ Vdc}, V_{BE} = 0, T_A = 65^{\circ}\text{C}$ )		I <sub>CES</sub>		0.5 3.0	μAdc

#### **ON CHARACTERISTICS(1)**

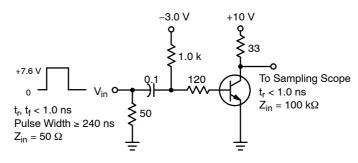
DC Current Gain	$(I_{C} = 30 \text{ mAdc}, V_{CE} = 0.4 \text{ Vdc})$ $(I_{C} = 100 \text{ mAdc}, V_{CE} = 0.5 \text{ Vdc})$ $(I_{C} = 300 \text{ mA}, V_{CE} = 1.0 \text{ Vdc})$	h <sub>FE</sub>	30 25 15	120 	—
Collector – Emitter Saturation Voltage		V <sub>CE(sat)</sub>		0.2 0.28 0.5 0.3	Vdc
Base – Emitter Saturation Voltage	(I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 3.0 mAdc) (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 10 mAdc) (I <sub>C</sub> = 300 mAdc, I <sub>B</sub> = 30 mA)	V <sub>BE(sat)</sub>	0.73 — —	0.95 1.2 1.7	Vdc

1. Pulse Test: Pulse Width  $\leq$  300 µs; Duty Cycle  $\leq$  2.0%.

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T <sub>A</sub> =	25°C unless otherwise noted) (Continued)
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	Symbol	Min	Max	Unit	
SMALL-SIGNAL	CHARACTERISTICS	L	L		
Current – Gain — E (I <sub>C</sub> = 30 mAdc, V	Bandwidth Product / <sub>CE</sub> = 10 Vdc, f = 100 MHz)	f <sub>T</sub>	350	_	MHz
Output Capacitanc (V <sub>CB</sub> = 5.0 Vdc,	e I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>		5.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)		C <sub>ibo</sub>		9.0	pF
	ARACTERISTICS	·			
Turn-On Time		t <sub>on</sub>	—	18	ns
Delay Time	(V <sub>CC</sub> = 10 Vdc, I <sub>C</sub> = 300 mAdc, I <sub>B1</sub> = 30 mAdc) (Figure 1)	t <sub>d</sub>	—	10	ns
Rise Time		t <sub>r</sub>	—	15	ns
Turn-Off Time	(V <sub>CC</sub> = 10 Vdc, I <sub>C</sub> = 300 mAdc, I <sub>B1</sub> = I <sub>B2</sub> = 30 mAdc)	t <sub>off</sub>	—	28	ns
Fall Time	(Figure 1)	t <sub>f</sub>		15	ns
Storage Time (V <sub>CC</sub> = 10 Vdc, I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = I <sub>B2</sub> = 10 mAdc) (Figure 2)		t <sub>s</sub>	—	18	ns





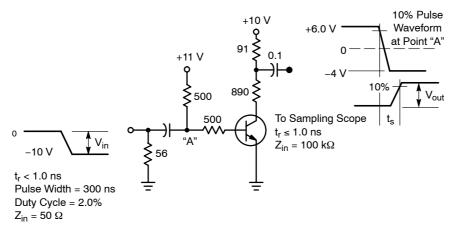
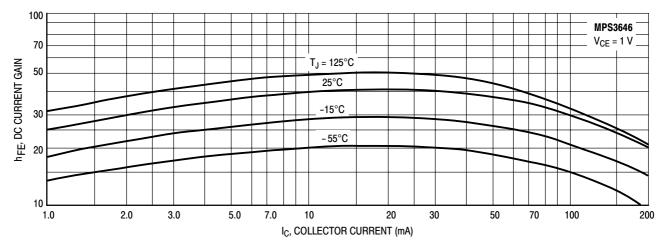
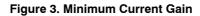


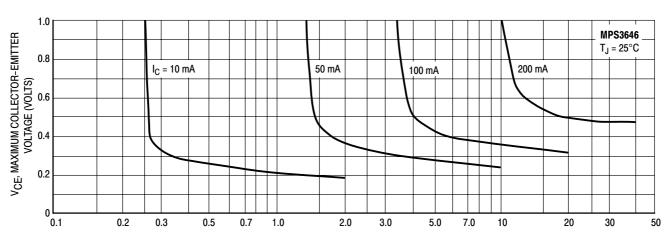
Figure 2. Charge Storage Time Test Circuit

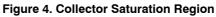
#### **CURRENT GAIN CHARACTERISTICS**

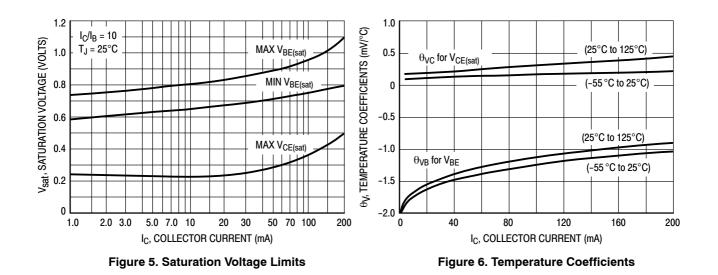




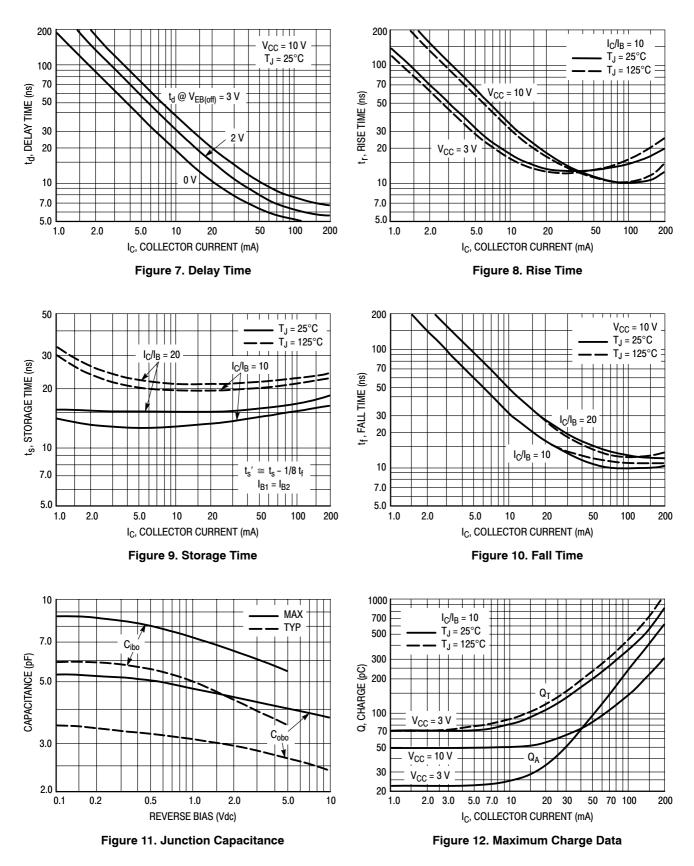
**"ON" CONDITION CHARACTERISTICS** 





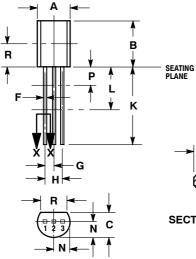


### **DYNAMIC CHARACTERISTICS**



## **PACKAGE DIMENSIONS**

CASE 029-11 (TO-226AA) ISSUE AD









NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. 4. DIMENSION F APPLIES BETWEEN P AND L DIMENSIONS D AND J APPLY BETWEEN L AND K MIMIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.135		3.43	

# <u>Notes</u>

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